

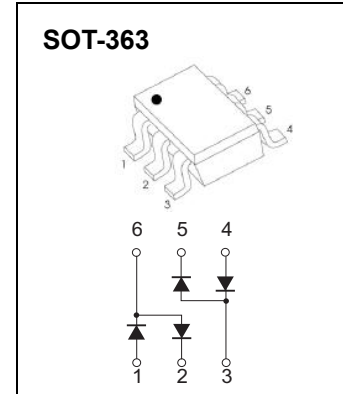
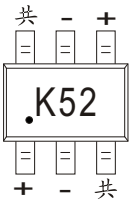
## Plastic-Encapsulate Diodes

Multi-Chip Diode

### FEATURES

- Surface Mount Package Ideally Suited for Automatic Insertion
- Very Low Leakage Current

### MARKING:K52



### Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25 °C

Symbol	Parameter	Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage	85	V
$V_{RWM}$	Working Peak Reverse Voltage		
$V_R$	DC Reverse Voltage	85	V
$I_O$	Average Rectified Output Current	160	mA
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current @t=8.3ms	1	A
$P_D$	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	°C/W
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55~+150	°C

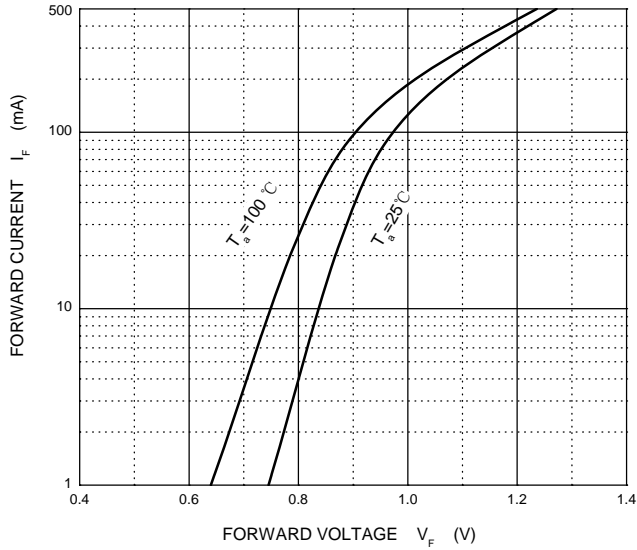
### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	85			V
Reverse voltage leakage current	$I_R$	$V_R=75V$			5	nA
Forward voltage	$V_F$	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$			0.9 1.0 1.1 1.25	V
Total capacitance	$C_{tot}$	$V_R=0V, f=1MHz$		2		pF
Reveres recovery time	$t_{rr}$	$I_F=I_R=10mA$ $I_{rr}=0.1I_R, R_L=100\Omega$			3	$\mu s$

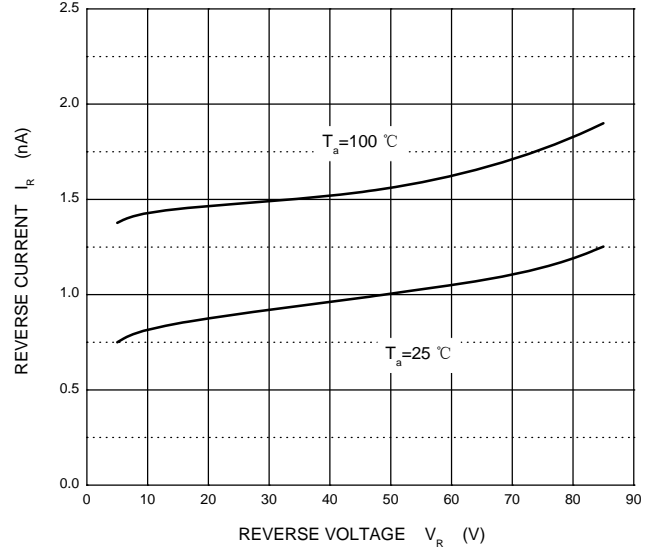


## Typical Characteristics

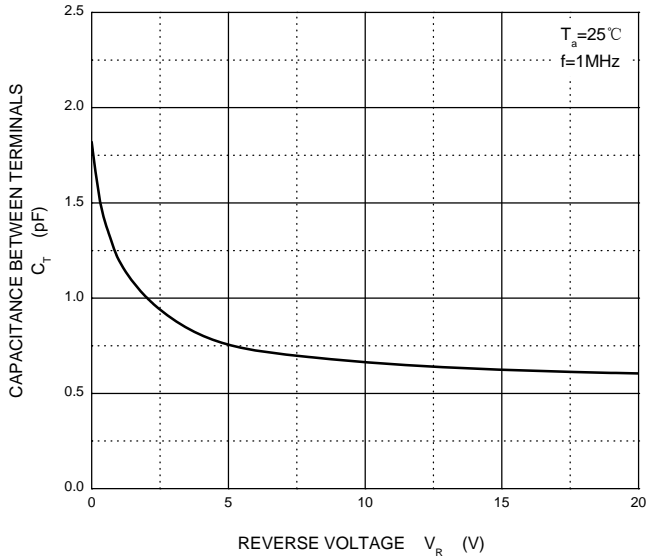
### Forward Characteristics



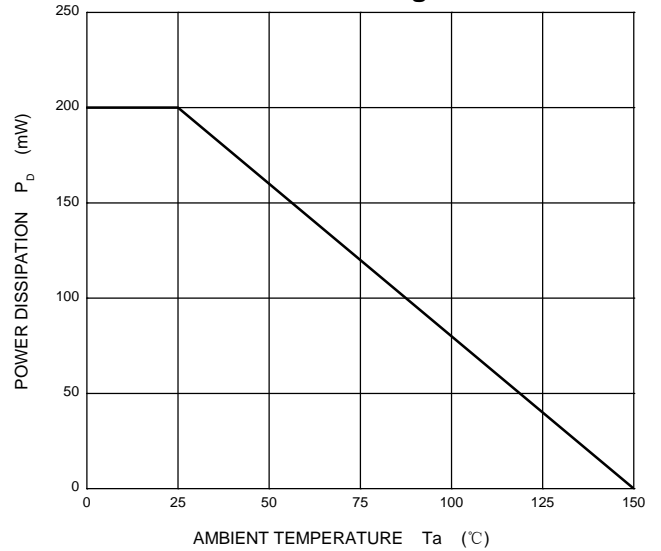
### Reverse Characteristics



### Capacitance Characteristics

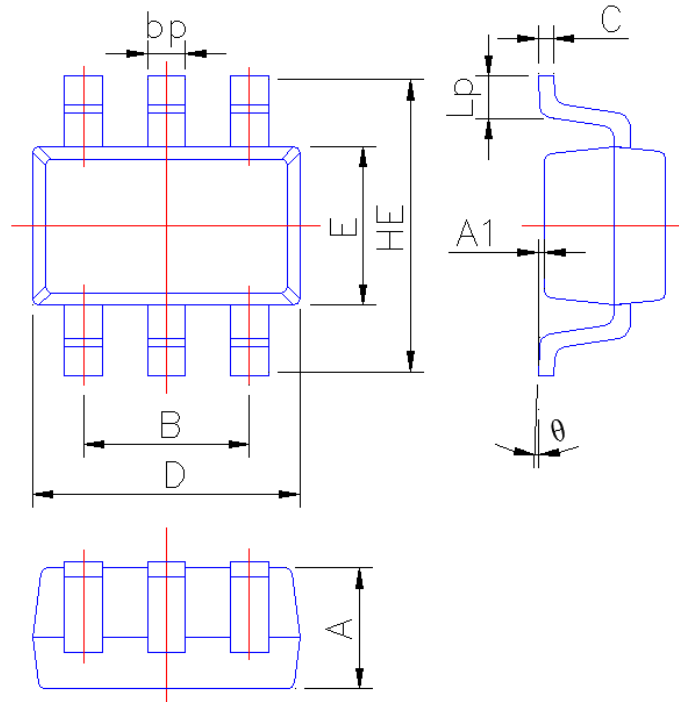


### Power Derating Curve





### SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°